

IC161P: APPLIED ELECTRONICS

Lab Exercise -2 Basics of BJT

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1.Abstract

To understand the basic characteristics of BJT.

2.Apparatus Required

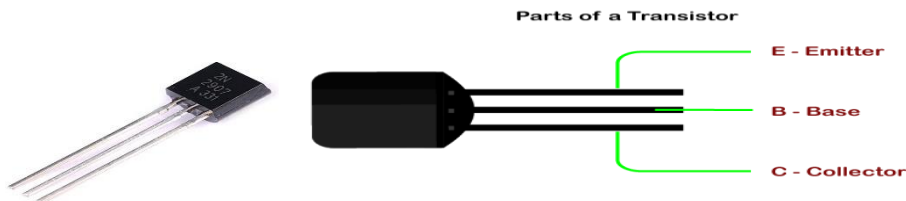
S.N.	Name
1	npn BJT
2	pnp BJT
3	Resistance
4	Power Supply
5	Connecting Wires

3.Theory

Transistor is an electronic semi-conductor device which is divided in two categories namely, BJT(Bipolar Junction Transistor) and FET(Field Effective Transistor).

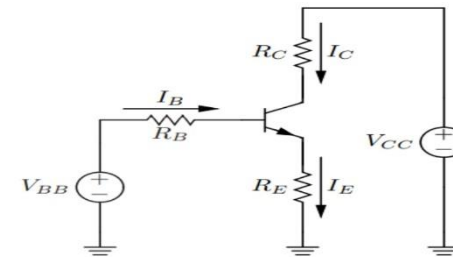
BJT has three terminals namely, emitter ,collector and emitter and is also divided in two categories namely, npn BJT(containg one p region between two n region) and pnp BJT(containg one n region between two p region).

Transistor Symbol

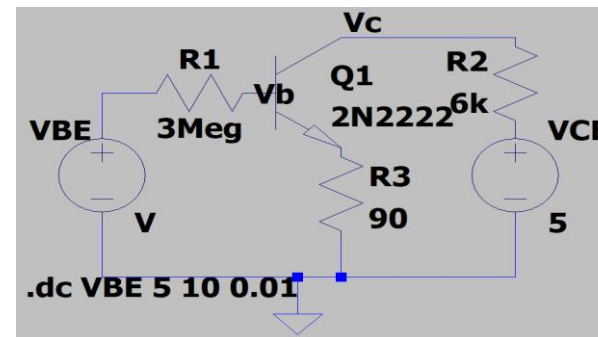


4.Circuit diagram and analysis

Experiment-1



- Set up the circuit shown, with $R_B = 3 \text{ M}\Omega$, $R_C = 6 \text{ k}\Omega$, and $R_E = 90 \Omega$. Set V_{CC} to 5 V.



a). Increase V_{BB} until $I_C = 0.5 \text{ mA}$. Measure V_{BE} and V_{BC} . What is the region of operation of the transistor?

Soln: V_{BE} and V_{BC} comes -637.41mV and 1362.59mV respectively.

The region of operation is Active Mode.

b). Considering above case measure I_B . What is the value of β ? And using this β find α and calculate I_E .

Soln: I_B comes $2.47\mu A$.

$$\beta = 500 / 2.471 = 202.44$$

$$\alpha = 202.435 / 203.435 = 0.995$$

$$I_E = 500 / 0.9951 = 502.47 \mu A$$

c). For $V_{BB} = 4 V$ and $V_{CC} = 2 V$. Measure I_B , I_C , V_{BE} , and V_{BC} . What is the region of operation of the BJT? Give reason for your answer.

Soln: I_B , I_C , V_{BE} and V_{BC} comes $1.22\mu A$, $224.09\mu A$, $636.50mV$ and $-18.69mV$.

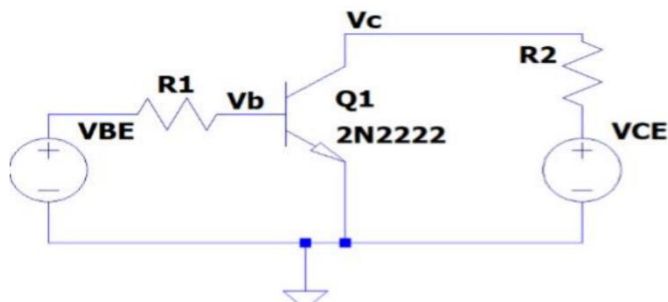
The region of operation is Active Mode as β is high and high voltage gain characteristics.

d). For $V_{BB} = -2 V$ and $V_{CC} = 5 V$. Measure I_B , I_C , V_{BE} , and V_{BC} . What is the region of operation of the BJT? Give reason for your answer.

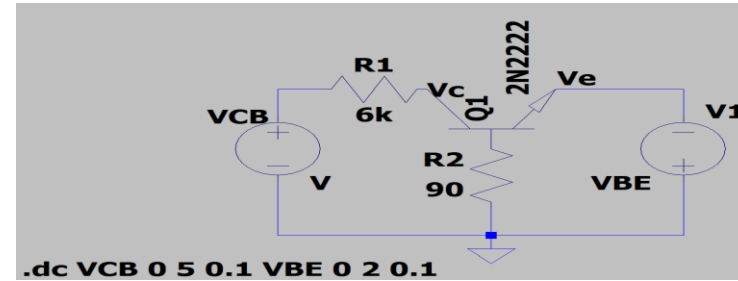
Soln: I_B , I_C , V_{BE} and V_{BC} comes $-9pA$, $7pA$, $-2V$ and $-7V$.

The region of operation is Cutoff Mode as both EB and CB junctions are reverse biased.

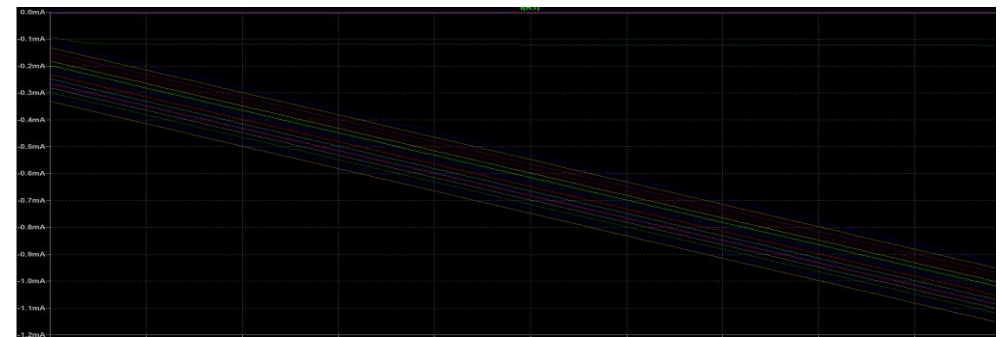
Experiment-2



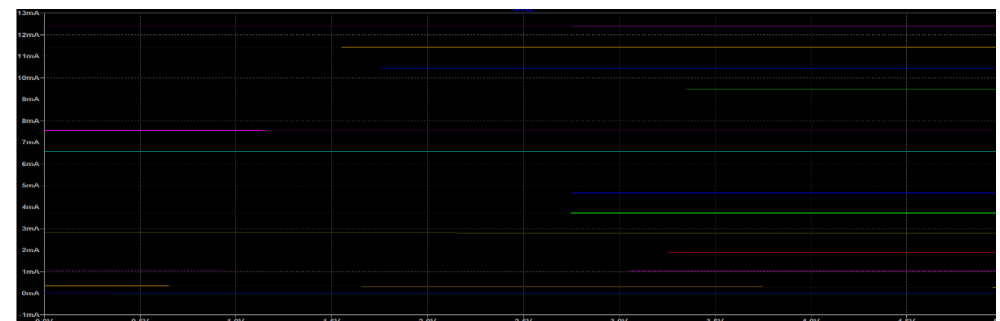
- In the above figure instead of V_{CE} now consider V_{CB} i.e., consider a CB mode configuration and obtain its input and output characteristics.



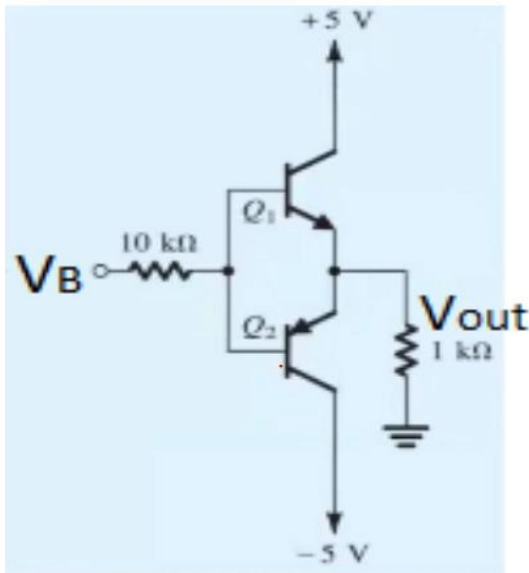
INPUT



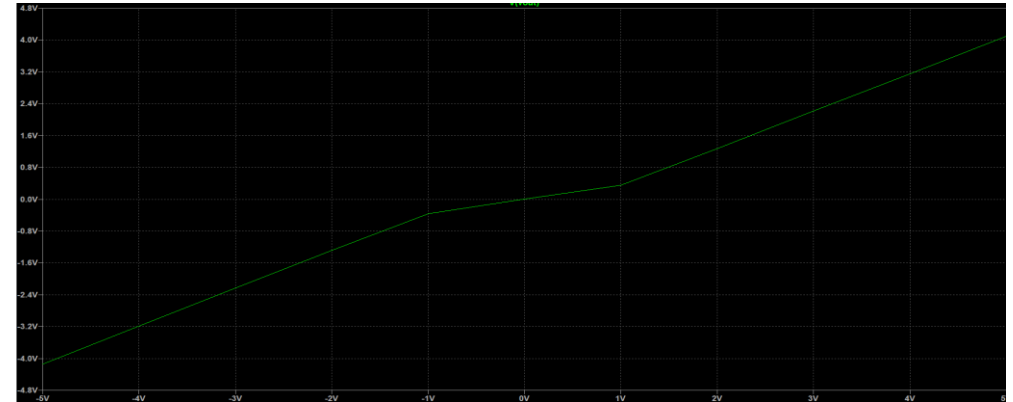
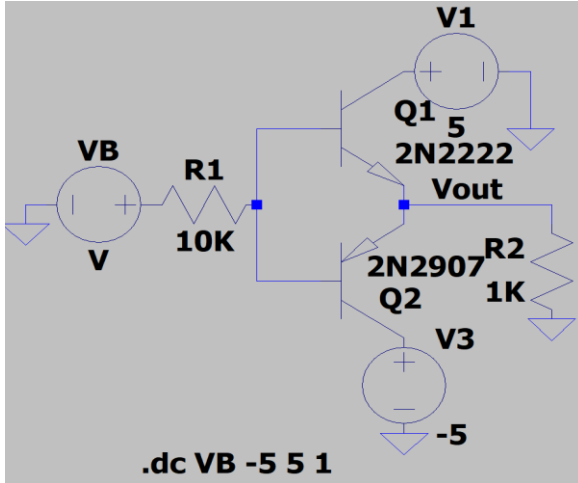
OUTPUT



Experiment-3



- In this setup vary V_B from -5V to +5V and plot V_{out} vs V_B . Using the plot identify the mode of operation for Q1 and Q2.



When V_B is positive, both Q1 and Q2 are in Reverse Active Mode of operation whereas when V_B is negative, both are in Saturation Mode of operation.

4. Result Analysis and Conclusion

From the above experiments, we get various results and informations.

In Active mode of operation, EB junction is FB and CB junction is RB, β is quite large compared to one and there is high gain in voltage whereas in Cutoff mode of operation, both EB and CB junctions are RB and there is no voltage gain.

In saturation Mode of operation, both EB and CB junctions are FB and there is low voltage gain. In Reverse Active Mode of operation, EB junction is RB and CB junction is FB and this mode has no ue or value.

Irrespective of fact that VBC is RB, IE is quite high is something interesting in Active Mode of operation.